

In the claims: The claims are as follows.

1. (Previously presented) A semiconductor capacitor having a first semiconductor layer which forms a first capacitor electrode (1) and which includes silicon, a second capacitor electrode (3) and a capacitor dielectric (5) including praseodymium oxide between the capacitor electrodes (1, 3), characterised in that provided between the capacitor dielectric (5) including praseodymium oxide and at least the first semiconductor layer (1) including silicon is a first thin intermediate layer (9) serving as a diffusion barrier for oxygen.
2. (Original) A semiconductor capacitor as set forth in claim 1 characterised in that the first thin intermediate layer (9) includes oxynitride or titanium.
3. (Original) A semiconductor capacitor as set forth in claim 1 or claim 2 wherein the thickness of the first thin intermediate layer (9) is 0.5 nm or less.
4. (Previously presented) A semiconductor capacitor as set forth in claim 1 wherein the second capacitor electrode (3) is formed from a second semiconductor layer and there is a second thin intermediate layer (11) between the second semiconductor layer and the capacitor dielectric (5) and the second semiconductor layer includes praseodymium.
5. (Original) A semiconductor capacitor as set forth in claim 4 wherein the second thin intermediate layer (11) includes oxynitride.
6. (Previously presented) A semiconductor capacitor as set forth in claim 4 wherein the second thin intermediate layer (11) includes silicon oxide.

7. (Previously presented) A semiconductor capacitor as set forth in claim 4 wherein the thickness of the second thin intermediate layer (11) is 0.5 nm or less.

8. (Previously presented) A semiconductor capacitor as set forth in claim 2 wherein the oxynitride of the first or the second thin intermediate layer (9, 11) has a concentration ratio of oxygen to nitrogen of 1:1.

9. (Previously presented) A memory cell for a dynamic random access memory, which includes a semiconductor capacitor as set forth in claim 1.

10. (Previously presented) A field effect transistor comprising a substrate (1), a gate oxide layer (5) and a gate electrode (3), which includes a semiconductor capacitor as set forth in claim 1, wherein the substrate (1) forms the first capacitor electrode, the gate electrode (3) forms the second capacitor electrode and the gate oxide (5) forms the capacitor dielectric.

11. (Previously presented) A semiconductor capacitor as set forth in claim 5 wherein the oxynitride of the first or the second thin intermediate layer (9, 11) has a concentration ratio of oxygen to nitrogen of 1:1.

12. (New) A semiconductor capacitor as set forth in claim 1 wherein the first thin intermediate layer (9) is titanium.